

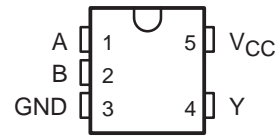
SN74AHC1G00

SINGLE 2-INPUT POSITIVE-NAND GATE

SCLS313G – MARCH 1996 – REVISED JANUARY 2000

- **EPIC™ (Enhanced-Performance Implanted CMOS) Process**
- **Operating Range 2-V to 5.5-V V_{CC}**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages**

DBV OR DCK PACKAGE
(TOP VIEW)



description

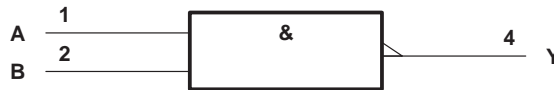
The SN74AHC1G00 performs the Boolean function $Y = \overline{A \bullet B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The SN74AHC1G00 is characterized for operation from -40°C to 85°C .

FUNCTION TABLE

| INPUTS | | OUTPUT |
|--------|---|--------|
| A | B | Y |
| H | H | L |
| L | X | H |
| X | L | H |

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



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**TEXAS
INSTRUMENTS**

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

| | |
|--|----------------------------|
| Supply voltage range, V_{CC} | –0.5 V to 7 V |
| Input voltage range, V_I (see Note 1) | –0.5 V to 7 V |
| Output voltage range, V_O (see Note 1) | –0.5 V to $V_{CC} + 0.5$ V |
| Input clamp current, I_{IK} ($V_I < 0$) | –20 mA |
| Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) | ±20 mA |
| Continuous output current, I_O ($V_O = 0$ to V_{CC}) | ±25 mA |
| Continuous current through V_{CC} or GND | ±50 mA |
| Package thermal impedance, θ_{JA} (see Note 2): DBV package | 347°C/W |
| DCK package | 389°C/W |
| Storage temperature range, T_{stg} | –65°C to 150°C |

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

| | | MIN | MAX | UNIT |
|---------------------|------------------------------------|--------------------------|----------|------|
| V_{CC} | Supply voltage | 2 | 5.5 | V |
| V_{IH} | High-level input voltage | $V_{CC} = 2$ V | 1.5 | V |
| | | $V_{CC} = 3$ V | 2.1 | |
| | | $V_{CC} = 5.5$ V | 3.85 | |
| V_{IL} | Low-level input voltage | $V_{CC} = 2$ V | 0.5 | V |
| | | $V_{CC} = 3$ V | 0.9 | |
| | | $V_{CC} = 5.5$ V | 1.65 | |
| V_I | Input voltage | 0 | 5.5 | V |
| V_O | Output voltage | 0 | V_{CC} | V |
| I_{OH} | High-level output current | $V_{CC} = 2$ V | –50 | μA |
| | | $V_{CC} = 3.3$ V ± 0.3 V | –4 | mA |
| | | $V_{CC} = 5$ V ± 0.5 V | –8 | |
| I_{OL} | Low-level output current | $V_{CC} = 2$ V | 50 | μA |
| | | $V_{CC} = 3.3$ V ± 0.3 V | 4 | mA |
| | | $V_{CC} = 5$ V ± 0.5 V | 8 | |
| $\Delta t/\Delta v$ | Input transition rise or fall rate | $V_{CC} = 3.3$ V ± 0.3 V | 100 | ns/V |
| | | $V_{CC} = 5$ V ± 0.5 V | 20 | |
| T_A | Operating free-air temperature | –40 | 85 | °C |

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | V _{CC} | T _A = 25°C | | | MIN | MAX | UNIT |
|-----------------|---|-----------------|-----------------------|-----|------|------|------|------|
| | | | MIN | TYP | MAX | | | |
| V _{OH} | I _{OH} = -50 µA | 2 V | 1.9 | 2 | | 1.9 | | V |
| | | 3 V | 2.9 | 3 | | 2.9 | | |
| | | 4.5 V | 4.4 | 4.5 | | 4.4 | | |
| | I _{OH} = -4 mA | 3 V | 2.58 | | | 2.48 | | |
| | I _{OH} = -8 mA | 4.5 V | 3.94 | | | 3.8 | | |
| V _{OL} | I _{OL} = 50 µA | 2 V | | | 0.1 | | 0.1 | V |
| | | 3 V | | | 0.1 | | 0.1 | |
| | | 4.5 V | | | 0.1 | | 0.1 | |
| | I _{OL} = 4 mA | 3 V | | | 0.36 | | 0.44 | |
| | I _{OL} = 8 mA | 4.5 V | | | 0.36 | | 0.44 | |
| I _I | V _I = V _{CC} or GND | 0 V to 5.5 V | | | ±0.1 | | ±1 | µA |
| I _{CC} | V _I = V _{CC} or GND, I _O = 0 | 5.5 V | | | 1 | | 10 | µA |
| C _i | V _I = V _{CC} or GND | 5 V | | 2 | 10 | | 10 | pF |

switching characteristics over recommended operating free-air temperature range,
V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | LOAD CAPACITANCE | T _A = 25°C | | | MIN | MAX | UNIT |
|------------------|--------------|-------------|------------------------|-----------------------|-----|------|-----|-----|------|
| | | | | MIN | TYP | MAX | | | |
| t _{PLH} | A or B | Y | C _L = 15 pF | | 5.5 | 7.9 | 1 | 9.5 | ns |
| t _{PHL} | | | | | 5.5 | 7.9 | 1 | 9.5 | |
| t _{PLH} | A or B | Y | C _L = 50 pF | | 8 | 11.4 | 1 | 13 | ns |
| t _{PHL} | | | | | 8 | 11.4 | 1 | 13 | |

switching characteristics over recommended operating free-air temperature range,
V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | LOAD CAPACITANCE | T _A = 25°C | | | MIN | MAX | UNIT |
|------------------|--------------|-------------|------------------------|-----------------------|-----|-----|-----|-----|------|
| | | | | MIN | TYP | MAX | | | |
| t _{PLH} | A or B | Y | C _L = 15 pF | | 3.7 | 5.5 | 1 | 6.5 | ns |
| t _{PHL} | | | | | 3.7 | 5.5 | 1 | 6.5 | |
| t _{PLH} | A or B | Y | C _L = 50 pF | | 5.2 | 7.5 | 1 | 8.5 | ns |
| t _{PHL} | | | | | 5.2 | 7.5 | 1 | 8.5 | |

operating characteristics, V_{CC} = 5 V, T_A = 25°C

| PARAMETER | | TEST CONDITIONS | TYP | UNIT |
|-----------------|-------------------------------|--------------------|-----|------|
| C _{pd} | Power dissipation capacitance | No load, f = 1 MHz | 9.5 | pF |

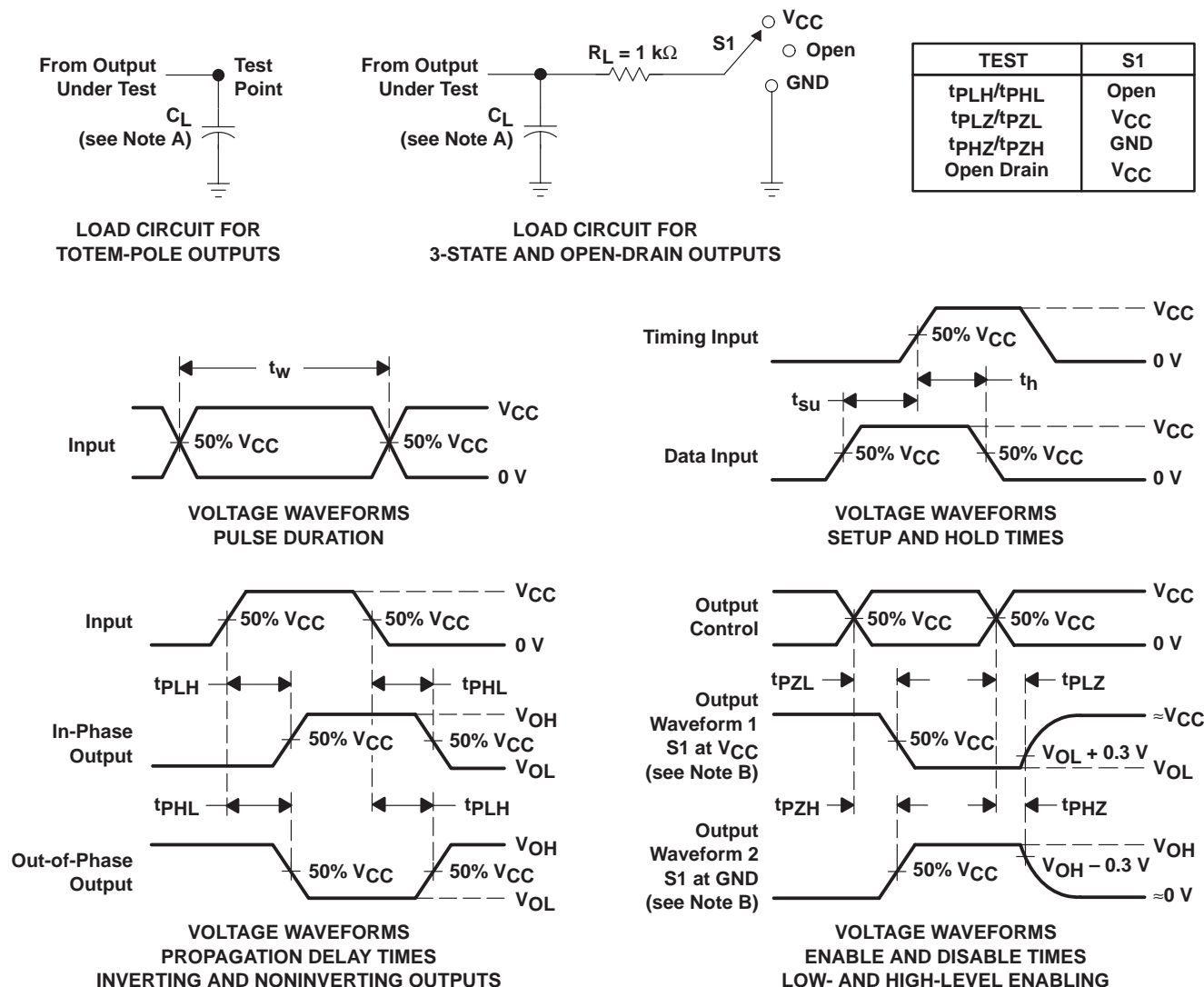


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PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{ MHz}$, $Z_O = 50\text{ }\Omega$, $t_r \leq 3\text{ ns}$, $t_f \leq 3\text{ ns}$.
- D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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